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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

**Complete if Known**

Application Number	10/780,317
Filing Date	February 17, 2004
First Named Inventor	Volker HARLE
Art Unit	
Examiner Name	
Attorney Docket Number	5367-69

Sheet 1 of 2

**U.S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind-Code <sup>2</sup> (if known)			
CX		US-5,831,277	11-03-1998	Razeghi	
CX		US-5,684,309	11-04-1997	McIntosh et al.	
CX		US-6,172,381 B1	01-09-2001	Nagahama et al.	
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**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>3</sup>
		Country Code <sup>3</sup> Number <sup>4</sup> Kind-Code <sup>5</sup> (if known)				
CX		WO 98/31055	07-16-1998	Nagahama et a.		
CX		WO 01/39282	05-31-2001	Harle et al.		Abstract
CX		EP 1 017 133	07-05-2000	Hattori et al.		
CX		EP 1 263 031 A1	04-12-2002	Koike et al		

Examiner  
Signature

Christy Kawasek

Date  
Considered

6/15/05

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Sheet	2	of	2	Attorney Docket Number	5367-69

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
CX	1.	Y.H. Song et al.: "Lateral Epitaxial Overgrowth of GaN and Its Crystallographic Tilt Depending on the Growth Condition", Phys. Stat. Sol. (a) 180, (2000), pp. 247-250	
CX	2.	S. Tanaka et al.: "Anti-Surfactant in III Nitride Epitaxy-Quantum Dot Formation and Dislocation Termination", Jpn. J. Appl. Phys. Vol. 39, pp. L831-L834 Part 2, No. 8Bd., 15 Aug. 2000	
CX	3.	Visconti et al.: "Dislocation density in GaN determined by photoelectrochemical and hot-wet Etching", Applied Physics Letters 77, No. 22, pp. 3532-3534, 27 Nov. 2000	
CX	4.	E. Feltn et al.: "Epitaxial Lateral Overgrowth of GaN on Silicon (111)", Phys. Stat. Sol. (a) 188, No. 2, pp. 733-737 (2001).	
CX	5.	T. Gehrke et al.: "Pendeo-Epitaxy of Gallium Nitride and Aluminum Nitride Films and Heterostructures on Silicon Carbide Substrate", MRS Internet J. Semicond. Res. 4S1, G3.2 (1999).	
CX	6.	P.R. Hagemann, et al.: "Improvement of the Optical and Structural Properties of MOCVD Grown GaN on Sapphire by an in-situ SiN Treatment", Phys. Stat. Sol. (a) 188, No. 2, (2001), pp. 659-662.	
CX	7.	X. Li et al.: "GaN Epitaxial Lateral Overgrowth and Optical Characterization", Applied Physics Letters (1998), Vol. 73, No. 9, pp. 1179-1181, 31 Aug. 1998.	
CX	8.	B. Beaumont et al.: "Epitaxial Lateral Overgrowth of GaN", Phys. Stat. Sol. (b) 227 (2001), No. 1, pp. 1-43	
CX	9.	T.S. Zheleva et al.: "Pendeo-Epitaxy - A New Approach for Lateral Growth of Gallium Nitride Structures", MRS Internet J. Nitride Semicond. Res. 4S1, G3.38 (1999)	
CX	10.	T. Wang et al.: "A new method for a great reduction of dislocation density in a GaN layer grown on a sapphire substrate", Journal of Crystal Growth 213 (2000), pp. 188-192.	
CX	11.	H. Watanabe et al.: "Crystallographic Structure of FIELO-GaN Films Studied by Scanning Reflection Electron Microscopy", Workshop on Nitride Semiconductors, IPAP Conf., Serial 1, pages 272-275	
CX	12.	K. J. Linthicum et al.: "Process Routes for Low Defect-Density GaN on Various Substrates Employing PENDEO-Epitaxial Growth Techniques", MRS Internet J. Nitride Semicond. Res. 4S1, G4.9 (1999)	

Examiner Signature	Christy Horacek	Date Considered	6/15/05
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